10/805,670

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/805670	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:01
L2	2	("5952692").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:01
L3	2	("5973356").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:01
L4	4	("6211531").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:02
L5	4	semiconductor adj memory adj element adj arrangement	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:03
L6	4	5 and (first or second or elctrically or insulating or substrate or electrode or trench or structure or arranged or parallel or structures or gate or polysilicon or nitride or oxide or silicon or elctrical or charge or floating or multiple or photolithography or trenches or pattern or opening or openings or size or feature or width or read or control or voltage or reading or controlling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:14

L7	2	2 and (first or second or elctrically or insulating or substrate or electrode or trench or structure or arranged or parallel or structures or gate or polysilicon or nitride or oxide or silicon or elctrical or charge or floating or multiple or photolithography or trenches or pattern or opening or openings or size or feature or width or read or control or voltage or reading or controlling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:44
L8	2	3 and (first or second or elctrically or insulating or substrate or electrode or trench or structure or arranged or parallel or structures or gate or polysilicon or nitride or oxide or silicon or elctrical or charge or floating or multiple or photolithography or trenches or pattern or opening or openings or size or feature or width or read or control or voltage or reading or controlling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:40
L9	1	"5705415".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:34
L10	1	"5691230".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:34
L11	1	"5646900".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:35
L12	1	"5644540".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:35
L13	1	"5640342".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:35
L14	1	"5616934".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:35
L15	1	"5593912".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:36
L16	1	"5574299".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:37
L17	1	"5497017".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:38
L18	1	"5504357".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:39
L19	1	"5497017".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:39

L20	4	4 and (first or second or elctrically or insulating or substrate or electrode or trench or structure or arranged or parallel or structures or gate or polysilicon or nitride or oxide or silicon or elctrical or charge or floating or multiple or photolithography or trenches or pattern or opening or openings or size or feature or width or read or control or voltage or reading or controlling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:40
L21	1	"5604357".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:42
L22	1	"5319229".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:42
L23	1	"5286994".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:43
L24	1	"5216262".PN.	USPAT; USOCR	OR	OFF	2006/09/23 18:44
L25	1	23 and (first or second or elctrically or insulating or substrate or electrode or trench or structure or arranged or parallel or structures or gate or polysilicon or nitride or oxide or silicon or elctrical or charge or floating or multiple or photolithography or trenches or pattern or opening or openings or size or feature or width or read or control or voltage or reading or controlling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:46
L26	1	19 and (first or second or elctrically or insulating or substrate or electrode or trench or structure or arranged or parallel or structures or gate or polysilicon or nitride or oxide or silicon or elctrical or charge or floating or multiple or photolithography or trenches or pattern or opening or openings or size or feature or width or read or control or voltage or reading or controlling)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 18:46
L27	4158	438/257	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03

L28	692	438/263	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03
L29	1711	438/264	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03
L30	1077	438/266	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03
L31	1500	438/270	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03
L32	2905	438/238	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03
L33	1680	438/381	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03
L34	1677	438/680	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03
L35	4719	438/692	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:03

L36	2849	438/706	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:04
L37	1866	438/723	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:04
L38	1060	438/724	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:04
L39	723	438/743	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:04
L40	463	438/744	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:04
L41	2071	438/700	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 19:04